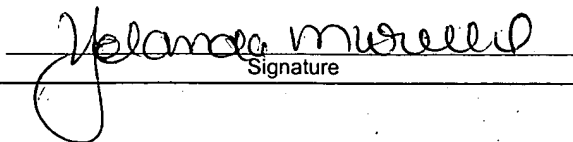


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Signature

**PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

DINESH CHOPRA

Group Art Unit: Unknown

Serial No.: Unknown

Examiner: Unknown

Filed: Concurrently Herewith

Atty. Dkt. No.: 2008.006382

For: METHOD OF REDUCING OXIDATION  
OF METAL STRUCTURES USING ION  
IMPLANTATION, AND DEVICE  
FORMED BY SUCH METHOD

Customer No.: 23720

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, it is respectfully requested that this Information Disclosure Statement be entered and the documents listed on attached Form PTO-1449 be considered by the Examiner and made of record.

In accordance with 37 C.F.R §§ 1.97(g),(h), this Information Disclosure Statement is not to be construed as a representation that a search has been made, and is not to be construed to be an admission that the information cited is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56(b).

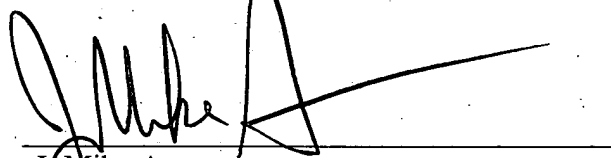
This application is a divisional application of Serial No. 10/229,457, filed August 28, 2002, and is relied upon for an earlier filing date under 35 U.S.C. § 120. In accordance with Rule 37 C.F.R. § 1.98(d) copies of the listed documents are not enclosed as they have been previously cited by or submitted to the Patent and Trademark Office in prior application Serial No. 10/229,457.

The present Information Disclosure Statement is being filed within three months of the filing date of this patent application or prior to the receipt of a first Official Action reflecting an examination on the merits, and hence is believed to be timely filed in accordance with 37 C.F.R. § 1.97(b). No fees are believed to be due in connection with the filing of this Information Disclosure Statement; however, should any fees under 37 C.F.R. §§ 1.16 to 1.21 be deemed necessary for any reason relating to these materials, the Director is hereby authorized to deduct said fees from Williams, Morgan & Amerson, P.C., Deposit Account No. 50-0786/2008.006382.

Applicant respectfully requests that the listed documents be made of record in the present case.

Respectfully submitted,

WILLIAMS, MORGAN & AMERSON  
CUSTOMER NO. 23720

A handwritten signature in black ink, appearing to read "J. Mike Amerson", is written over a horizontal line.

Date: October 9, 2003

J. Mike Amerson  
Reg. No. 35,426  
10333 Richmond, Suite 1100  
Houston, Texas 77042  
(713) 934-4055  
(713) 934-7011 (facsimile)

ATTORNEY FOR APPLICANT

Form PTO-1449 (modified)		Atty. Docket No. 2008.006382	Serial N . Unknown
List of Patents and Publications for Applicant's INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)		Applicants Dinesh Chopra	
		Filing Date: Concurrently Herewith	Group: 2822
U.S. Patent Documents See Page 1	Foreign Patent Documents See Page 1	Other Art See Page 1	

### U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
	A1	6,046,108	4/04/00	Liu <i>et al.</i>	438	687	
	A2	6,117,770	9/12/00	Pramanick <i>et al.</i>	438	659	
	A3	6,268,291 B1	7/31/01	Andricacos <i>et al.</i>	438	694	
	A4	6,281,127 B1	8/28/01	Shue	438	691	
	A5	6,426,289 B1	7/30/02	Farrar	438	670	
	A6	6,500,749 B1	12/31/02	Liu <i>et al.</i>	438	618	3/19/01

### Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
	B1	JP10041298A	2/13/98	Japan	H01L	021/3205	Abstract only
	B2						
	B3						

### Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation
	C1	Shibata <i>et al.</i> , "Lithography-less Ion Implantation Technology for Agile Fab," ULVAC Confidential
	C2	Shibata <i>et al.</i> , "Stencil Mask Ion Implantation Technology for High Performance MOSFETs," 2000 IEEE
	C3	

EXAMINER:

DATE CONSIDERED:

EXAMINER: INITIAL IF REFERENCE CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.